



《风光欣》技术资料

2SB1424

PNP TRANSISTOR

Features

Low $V_{CE(sat)}$

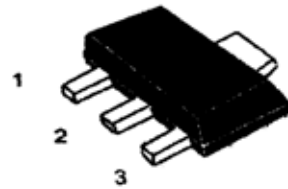
$V_{CE(sat)} = -0.2V(Typ)(I_c/I_B = -2A/-0.1A)$

Excellent DC current gain characteristics

● ABSOLUTE MAXIMUM RATINGS($T_A = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter -Base Voltage	V_{EBO}	-6	V
Collector Current	I_c	-3	A
Collector Dissipation	P_c	600	mW
Junction Temperature	T_j	150	
Storage Temperature	T_{STG}	-55 ~ +150	

SOT-89



1,Base 2,Collector 3,Emitter

● Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-20	—	—	V	$I_c = -50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-20	—	—	V	$I_c = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	-6	—	—	V	$I_E = -50 \mu A$
Collector cutoff current	I_{CBO}	—	—	-0.1	μA	$V_{CB} = -20V$
Emitter cutoff current	I_{EBO}	—	—	-0.1	μA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.5	V	$I_c/I_B = -2A/-0.1A$
DC current transfer ratio	h_{FE}	120	—	390	—	$V_{CE} = -2V, I_c = -0.1A$
Transition frequency	f_r	—	240	—	MHz	$V_{CE} = -2V, I_E = 0.5A, f = 100MHz$
Output capacitance	C_{ob}	—	35	—	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$

h_{FE} values are classified as follows :

Item	Q	R
h_{FE}	120~270	180~390